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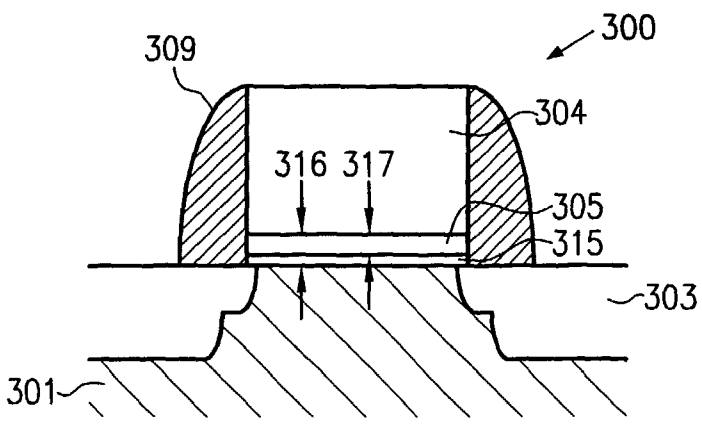
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(54) Title: TRANSISTOR ELEMENT HAVING AN ANISOTROPIC HIGH-K GATE DIELECTRIC



(57) Abstract: A field effect transistor 300 comprises a gate insulation layer including an anisotropic dielectric 305. The orientation is selected such that a first permittivity parallel to the gate insulation layer is significantly less than a second permittivity perpendicular to the gate insulation layer.

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